

Notice of References Cited	Application/Control No. 10/606,134		Applicant(s)/Patent Under Reexamination FRANCOM ET AL.	
	Examiner Elias Desta		Art Unit 2857	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-4,989,062	01-1991	Takahashi et al.	257/207
	B	US-2001/0054509	12-2001	Fujikami et al.	174/125.1
	C	US-6,028,440	02-2000	Roethig et al.	324/765
	D	US-6,741,086	05-2004	Maekawa et al.	324/754
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)			
	U	Keyes, 'Fundamental Limits of Silicon Technology', March 2001, IEEE Article, Vol. 89, No. 3, pages 227-239			
	V	Rosenthal et al., 'MHD Modeling of Conductors at Ultra-High Current Density', January 2000, IEEE Article, pages 1-20			
	W	Sakai et al., 'Critical Current Densities and Management Hysteresis Losses in Sub-Micron Filament Bronze Processed Nb3Sn Wires', March 1993, IEEE Article, Vol. 3, No. 1, pages 990-993			
	X				

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.